TOSHIBA Transistor Silicon PNP Triple Diffused Type

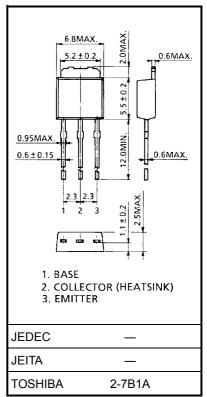
# 2SA1923

High Voltage Switching Applications

- High voltage: V<sub>CEO</sub> = -400 V
- Low saturation voltage: V<sub>CE</sub> (sat) = -1 V (max) (I<sub>C</sub> = -100 mA, I<sub>B</sub> = -10 mA)

#### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	-400	V	
Collector-emitter voltage		V <sub>CEO</sub>	-400	V	
Emitter-base voltage		V <sub>EBO</sub>	-7	V	
Collector current	DC	Ι <sub>C</sub>	-0.5	A	
	Pulse	I <sub>CP</sub>	-1		
Base current		I <sub>B</sub>	-0.25	А	
Collector power dissipation	Ta = 25°C	D.	1	W	
	Tc = 25°C	PC	10		
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



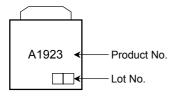
Weight: 0.36 g (typ.)

Unit: mm

## Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off c	current	I <sub>CBO</sub>	V <sub>CB</sub> = -400 V, I <sub>E</sub> = 0		—	-10	μA
Emitter cut-off cu	rrent	I <sub>EBO</sub>	$V_{EB} = -7 V, I_C = 0$		_	-1	μA
Collector-emitter	breakdown voltage	V (BR) CEO	I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0	-400	_	_	V
DC current gain		h <sub>FE (1)</sub>	$V_{CE} = -5 V, I_C = -20 mA$	140	_	450	
		h <sub>FE (2)</sub>	$V_{CE} = -5 V, I_C = -100 mA$	140	_	400	
Collector-emitter	saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = -100 mA, I <sub>B</sub> = -10 mA	_	-0.4	-1.0	V
Base-emitter satu	iration voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = -100 mA, I <sub>B</sub> = -10 mA	_	-0.76	-0.9	V
Transition frequency		f <sub>T</sub>	$V_{CE} = -5 V, I_C = -50 mA$	_	35	_	MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	18	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$20 \ \mu s \qquad \text{INPUT} \qquad \downarrow B1 \qquad \text{OUTPUT} \\ \downarrow I_{B2} \qquad \downarrow B2 \qquad \downarrow B2 \qquad \lor V_{CC} = -200 \ V$	_	0.2	_	
	Storage time	t <sub>stg</sub>		_	2.3	_	μs
	Fall time	t <sub>f</sub>	I <sub>B1</sub> = −10 mA, I <sub>B2</sub> = 20 mA, DUTY CYCLE ≤ 1%	_	0.2	_	

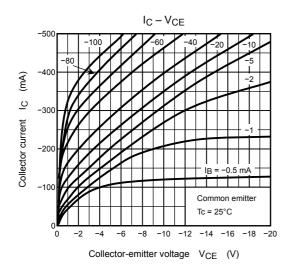
### Marking

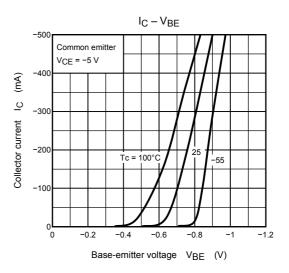


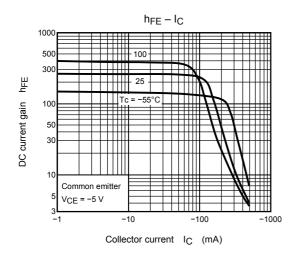
### Explanation of Lot No.

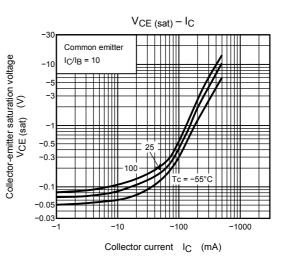
Month of manufacture: January to December are denoted by letters A to L respectively. Year of manufacture: last decimal digit of the year of manufacture

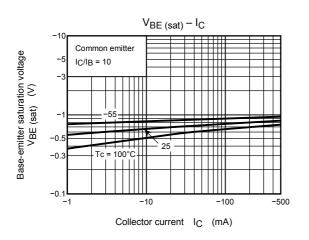
# TOSHIBA

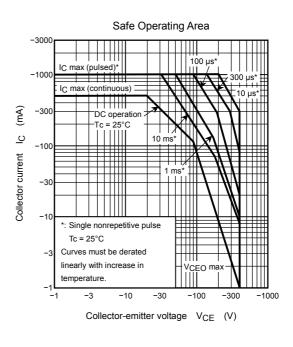












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